

JX075C 12A Sensitive SCR

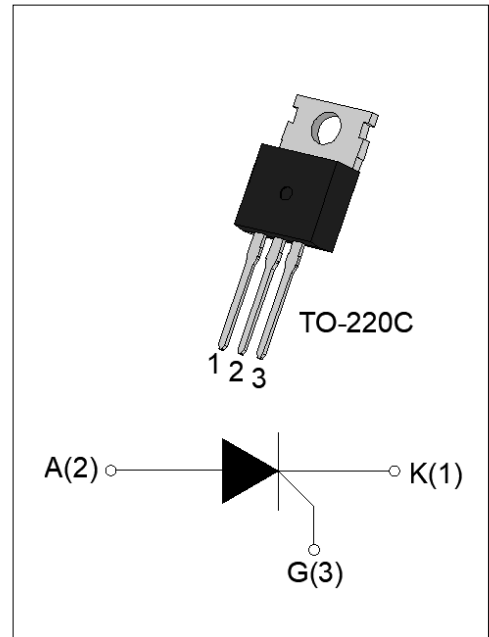
Rev.A.1.1

DESCRIPTION:

The JX075C SCR provides high dV/dt rate with strong resistance to electromagnetic interface. It is especially recommended for use on residual current circuit breaker, straight hair, igniter etc. Package TO-220C is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM} / V_{RRM}	800	V
I_{GT}	≤ 200	μA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range	T_j	-40-110	$^{\circ}C$
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	800	V
Average on-state current ($T_c \leq 89^{\circ}C$)	$I_{T(AV)}$	7.5	A
RMS on-state current ($T_c \leq 89^{\circ}C$)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current ($t_p=10ms$, $T_j=25^{\circ}C$)	I_{TSM}	120	A
Non repetitive surge peak on-state current ($t_p=8.3ms$, $T_j=25^{\circ}C$)		130	
I^2t value for fusing ($t_p=10ms$, $T_j=25^{\circ}C$)	I^2t	72	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=110^{\circ}C$)	di/dt	100	$A/\mu s$
Peak gate current ($t_p=20\mu s$, $T_j=110^{\circ}C$)	I_{GM}	4	A
Average gate power dissipation ($T_j=110^{\circ}C$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W

Peak pulse voltage ($T_j=25^{\circ}\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	0.5	kV
--	----------	-----	----

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	-	60	200	μA
V_{GT}		-	-	0.8	V
V_{GD}	$V_D=V_{DRM}$ $T_j=110^{\circ}\text{C}$	0.2	-	-	V
I_L	$I_G=1.2 I_{GT}$	-	-	6	mA
I_H	$I_T=0.05\text{A}$	-	-	5	mA
dV/dt	$V_D=540\text{V}$ $T_j=25^{\circ}\text{C}$ $R_{GK}=1\text{k}\Omega$	50	-	-	V/ μs
	$V_D=540\text{V}$ $T_j=25^{\circ}\text{C}$ $R_{GK}=220\Omega$	200	-	-	
t_{on}	$I_G=10\text{mA}$ $I_A=20\text{mA}$ $I_R=2\text{mA}$ $T_j=25^{\circ}\text{C}$	-	2	-	μs
t_{off}		-	70	-	μs

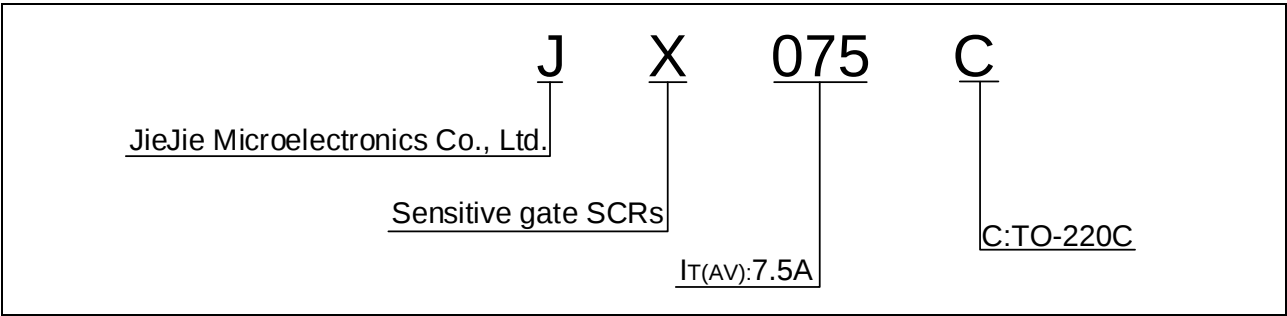
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_T=24\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.6	V
V_{TO}	Threshold voltage	$T_j=110^{\circ}\text{C}$	0.9	V
R_D	Dynamic Resistance	$T_j=110^{\circ}\text{C}$	0.02	Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=110^{\circ}\text{C}$	0.5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	1.3	$^{\circ}\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (DC)	40	$^{\circ}\text{C}/\text{W}$

ORDERING INFORMATION



MARKING

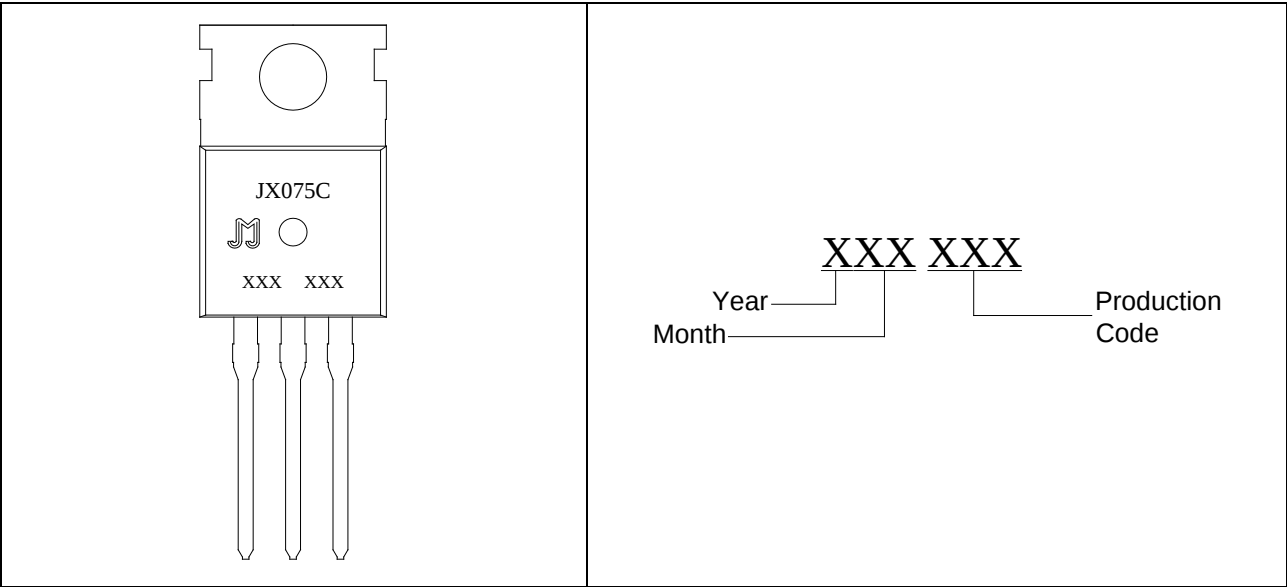


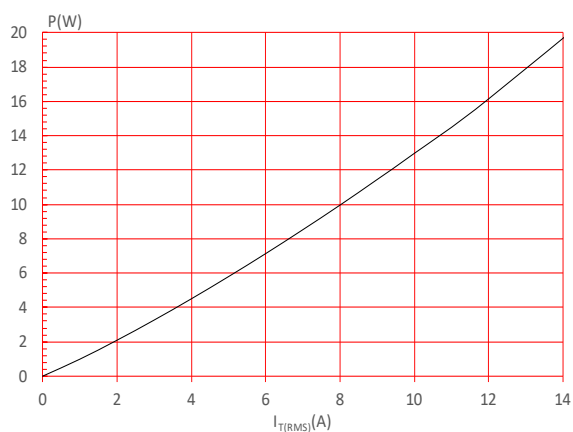
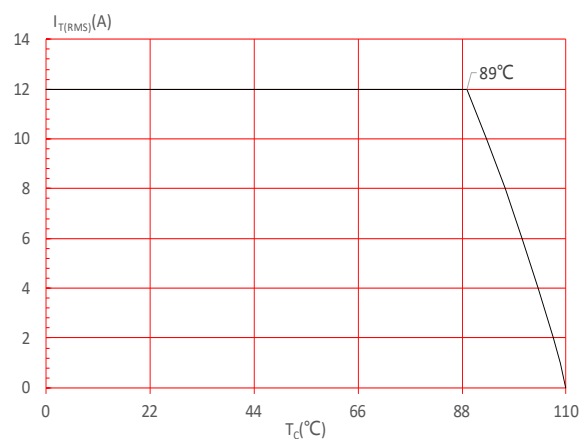
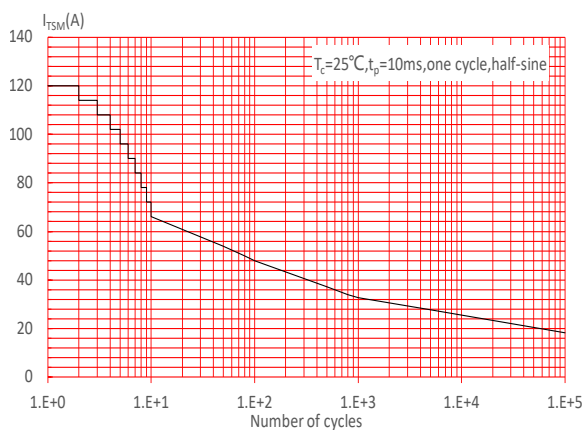
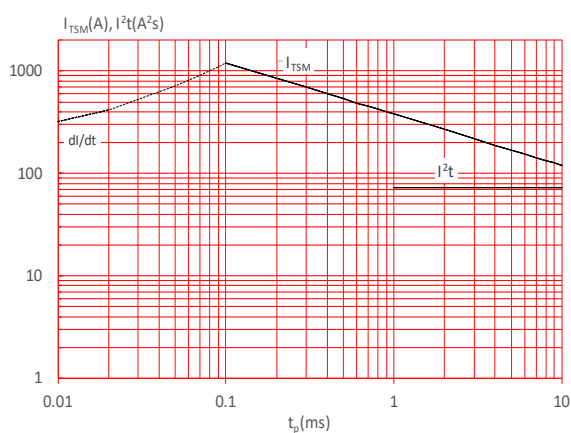
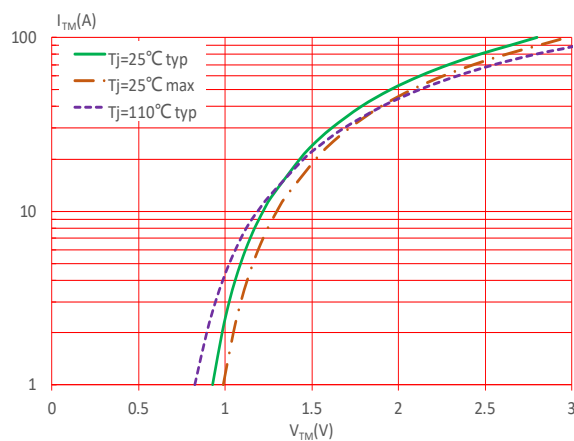
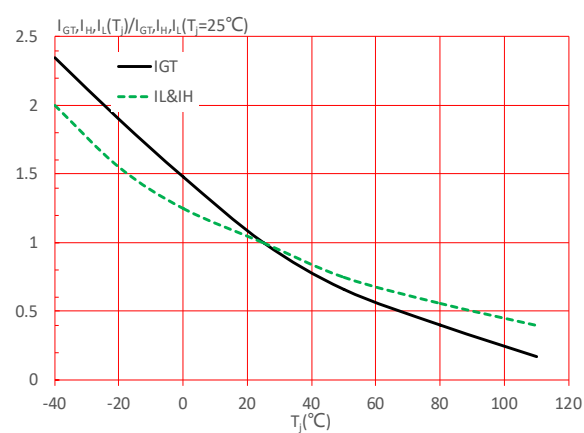
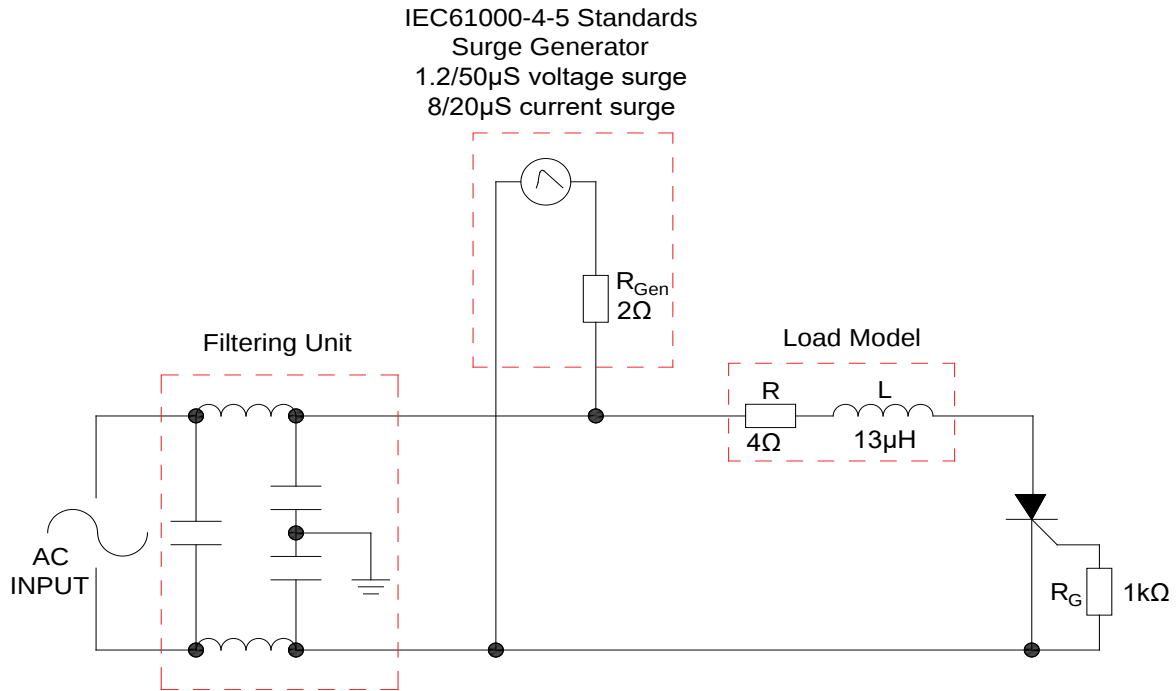
FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.3: Surge peak on-state current versus number of cycles

FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

FIG.4: On-state characteristics

FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

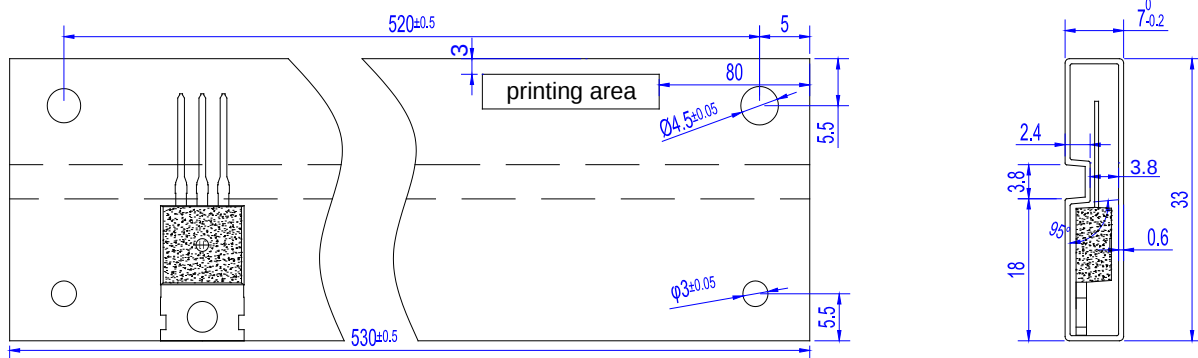
ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(μA)	Package	Base qty. (pcs)	Delivery mode
JX075C	800	≤ 200	TO-220C	50	Tube

Document Revision History

Date	Revision	Changes
Apr.12, 2023	A.1.0	Last update
Oct.15, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220C	TUBE	50	1,000	5,000

Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement.

Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.



is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.

Copyright © 2025 Jiangsu JieJie Microelectronics Co., Ltd. All rights reserved.